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Vishinsky

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(54) **SAMPLE-AND-HOLD CIRCUIT WITH ENHANCED NOISE LIMIT**

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H03K 17/687 (2006.01)
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H03M 1/12 (2006.01)
H02M 1/00 (2006.01)

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CPC **H03K 17/6872** (2013.01); **G11C 27/02** (2013.01); **H03M 1/124** (2013.01); **H02M 2001/0009** (2013.01)

(58) **Field of Classification Search**
None
See application file for complete search history.

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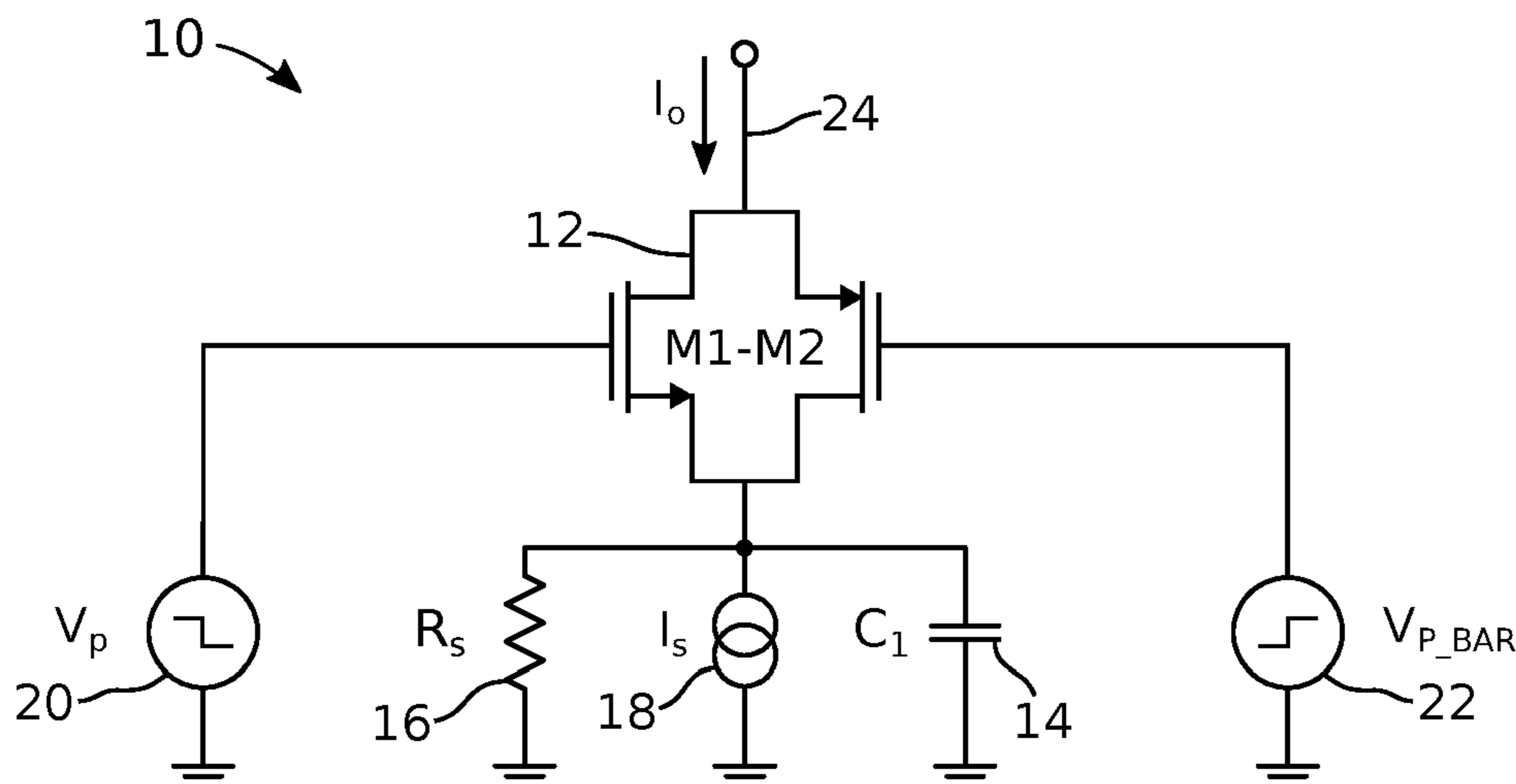
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(57) **ABSTRACT**

A sample-and-hold circuit is presented that is current driven at the input and current sensed at the output, using two capacitors—one at the input to the ground and second past a pair of complementary CMOS switches at the output to the ground. These capacitors in connection with an input current drive form a highpass noise transfer function that substantially reduces the 1/f noise of the switches and then rolls the transfer function off, further reducing the noise. The overall noise level is significantly lower as compared to a conventional voltage-driven and voltage-sensed sample-and-hold circuit that has a lowpass transfer function which, after integration, demonstrates a noise limit of kT/C . Depending on the circuit parameters the present sample-and-hold circuit shows an integrated noise improvement of between 5 and 10 dB over kT/C limit.

13 Claims, 4 Drawing Sheets



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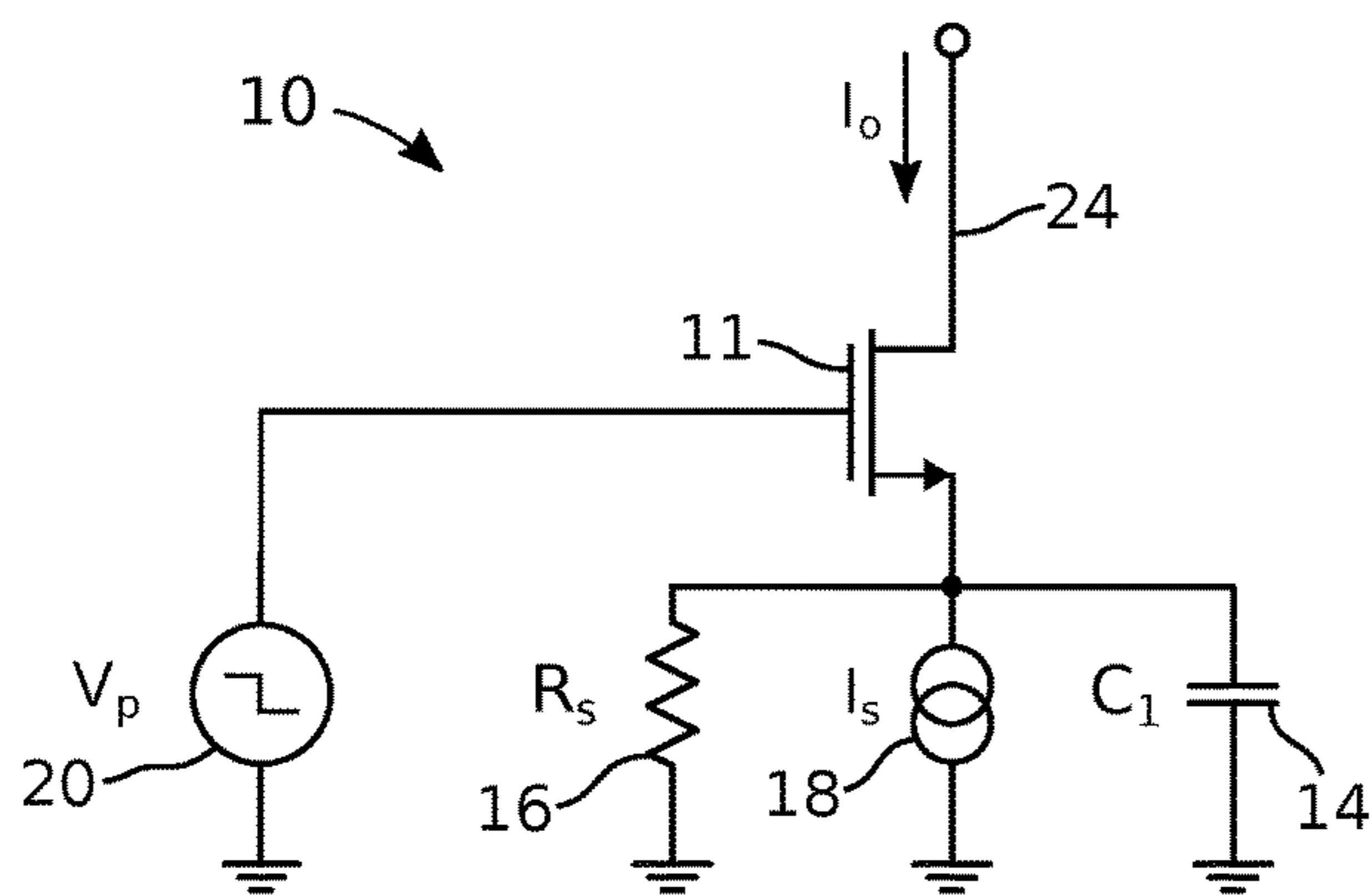


Fig. 1A

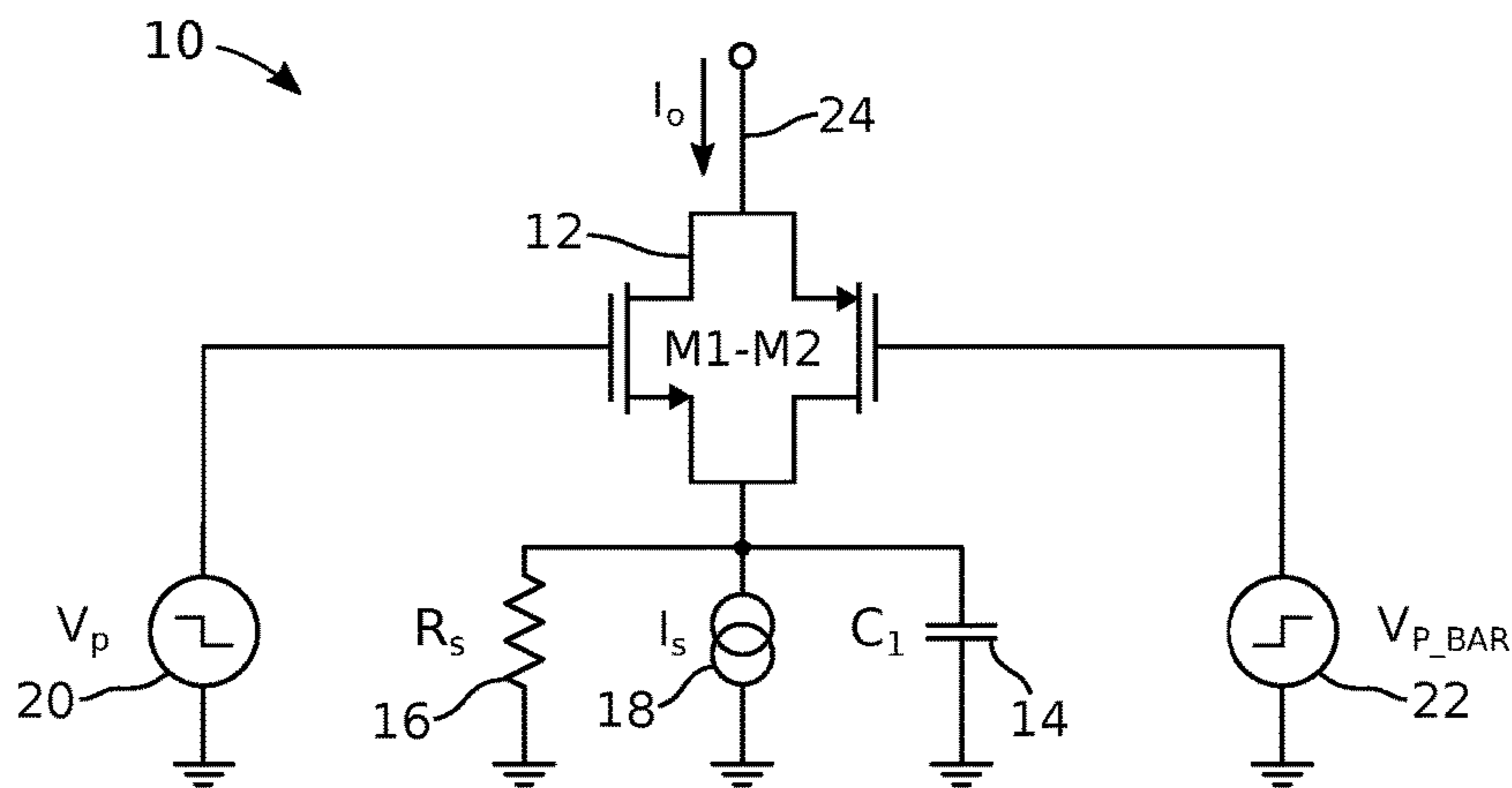


Fig. 1B

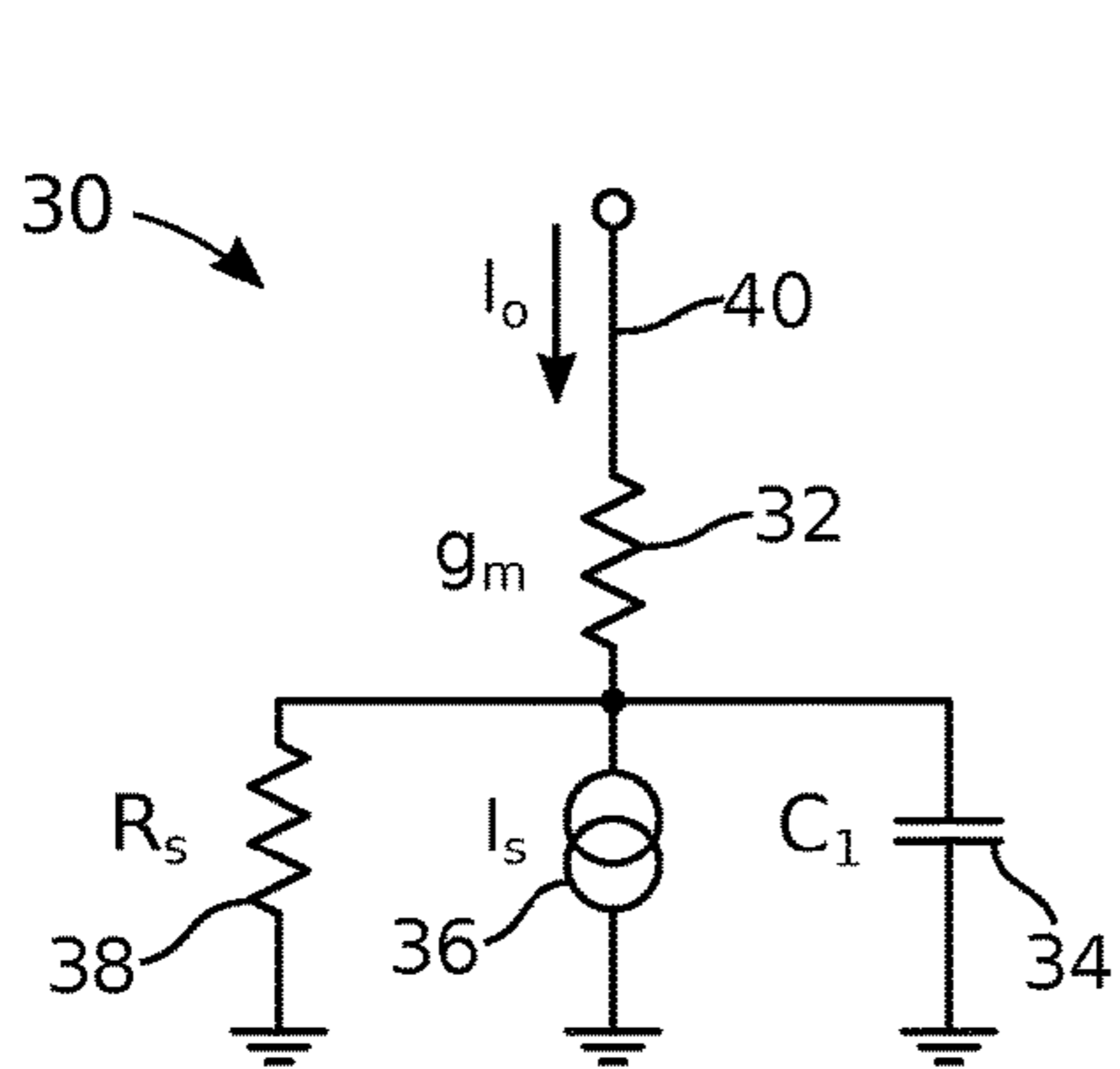


Fig. 2

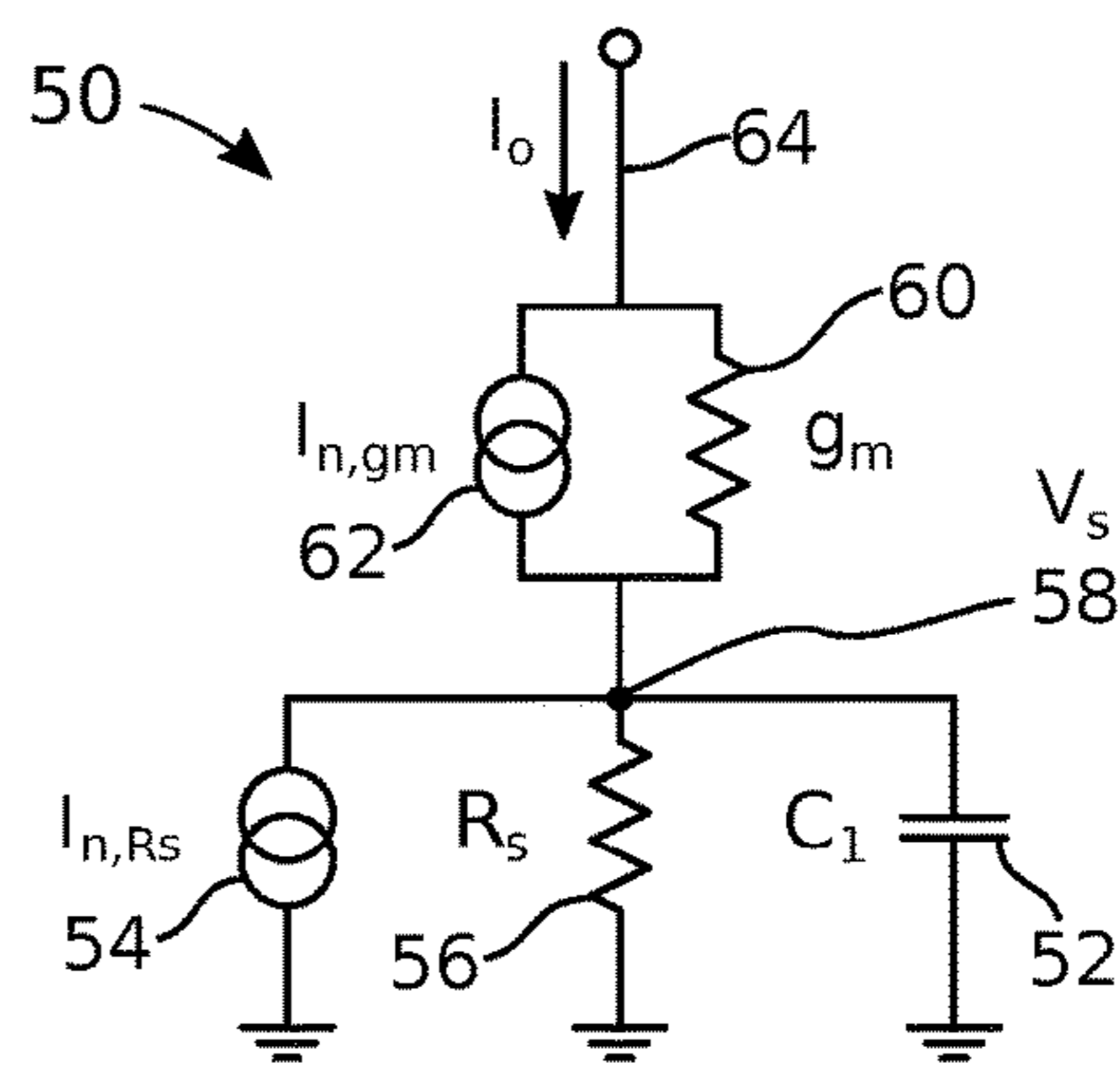


Fig. 3

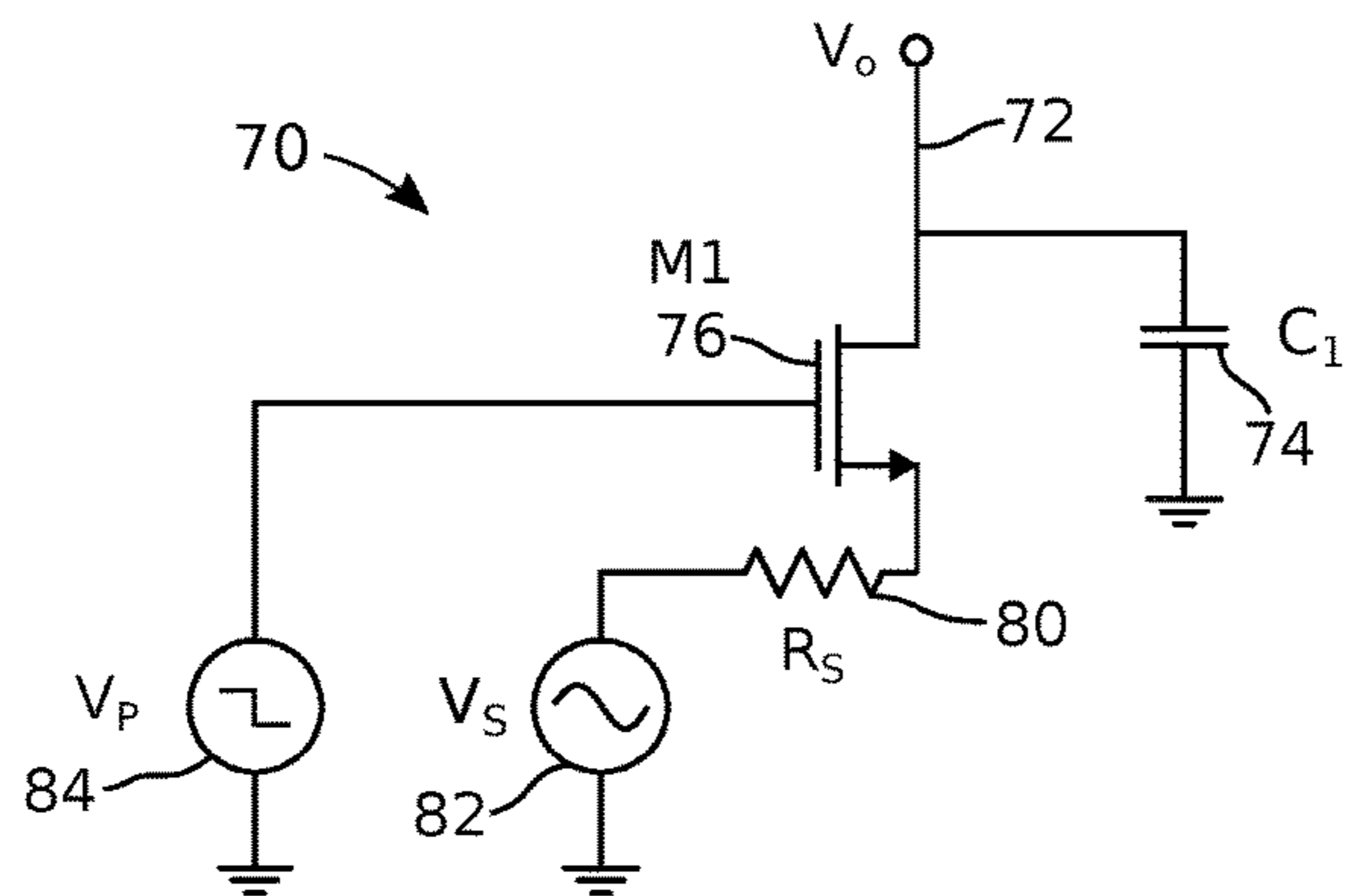


Fig. 4

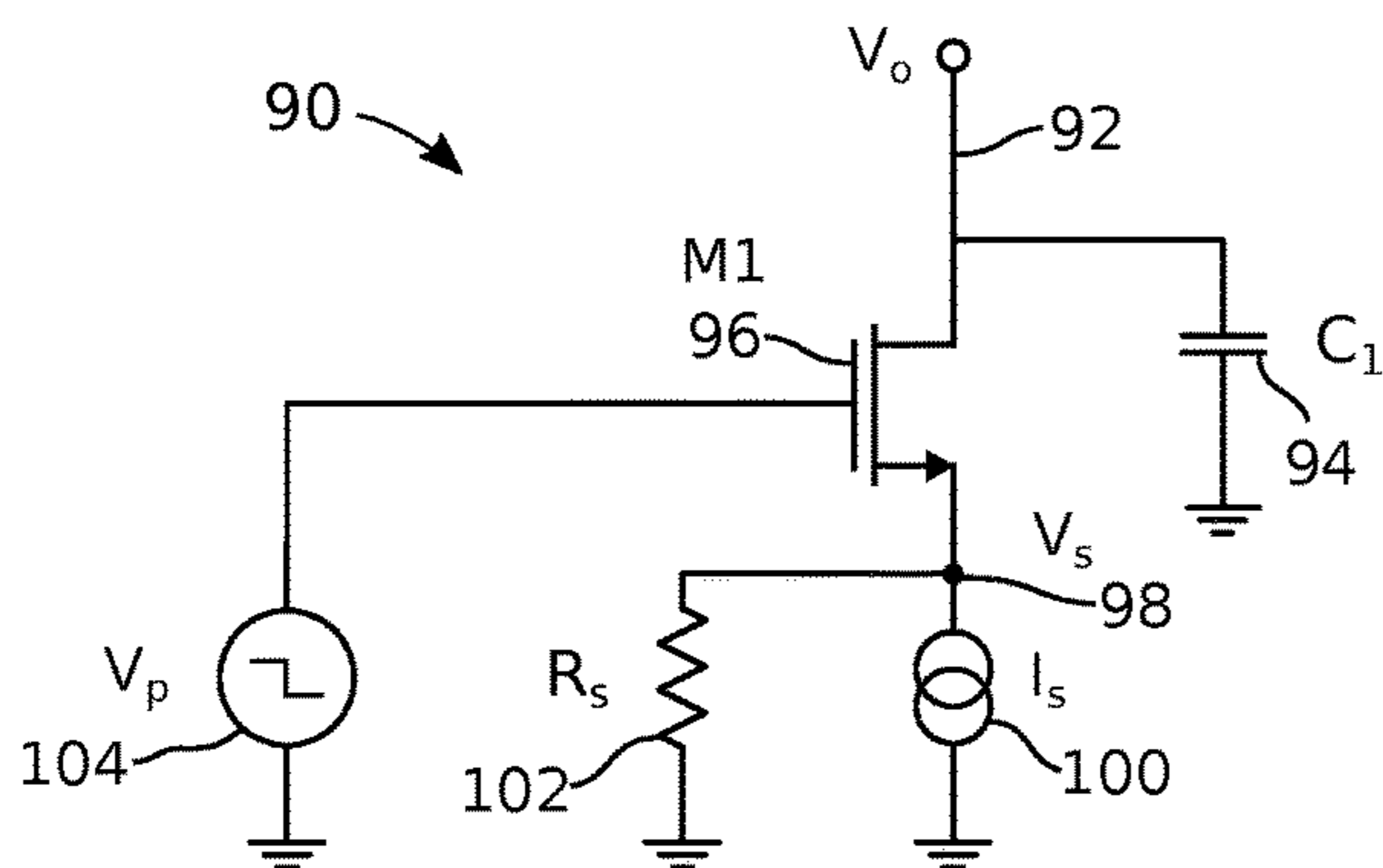


Fig. 5

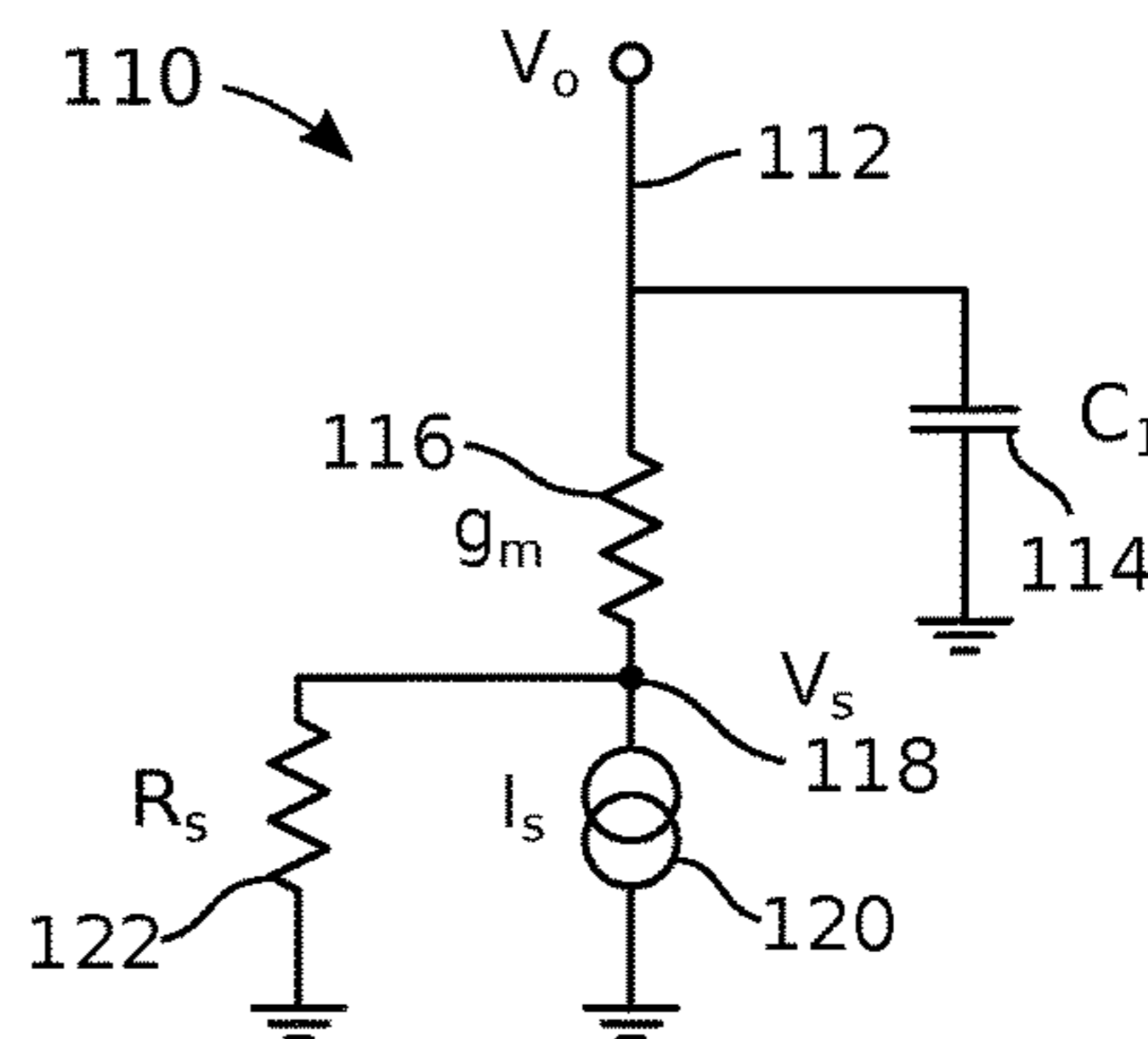


Fig. 6

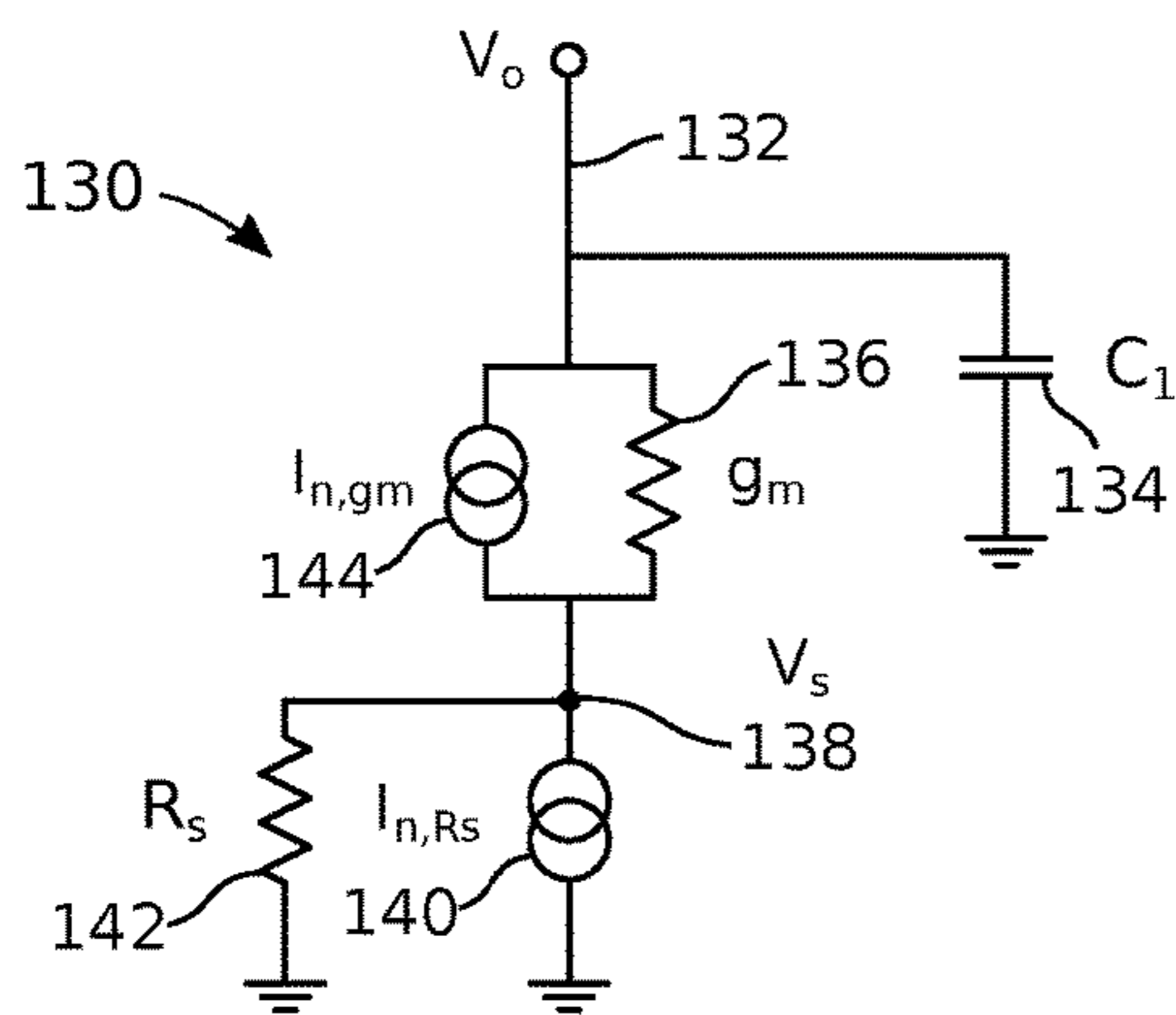


Fig. 7

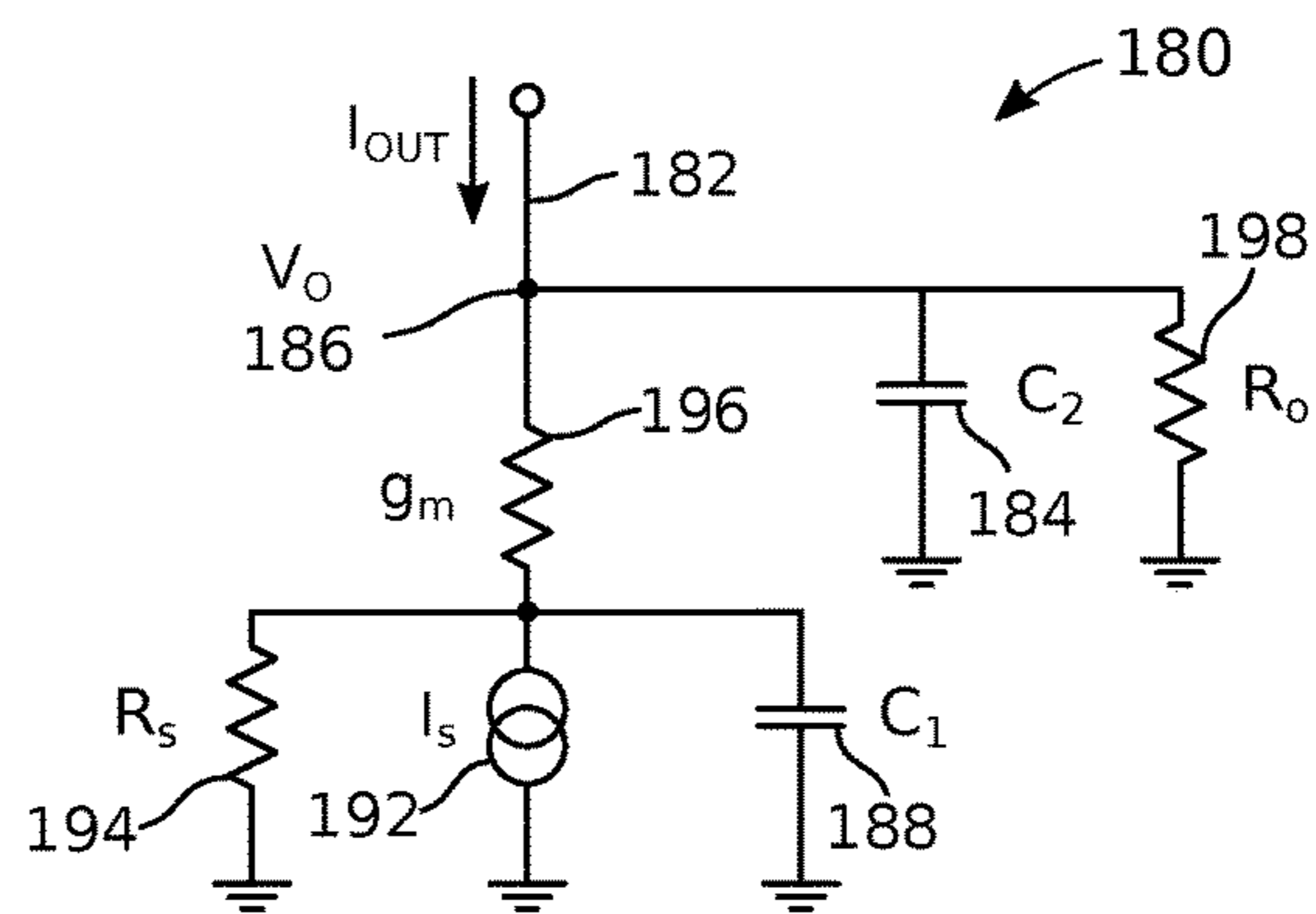


Fig. 11

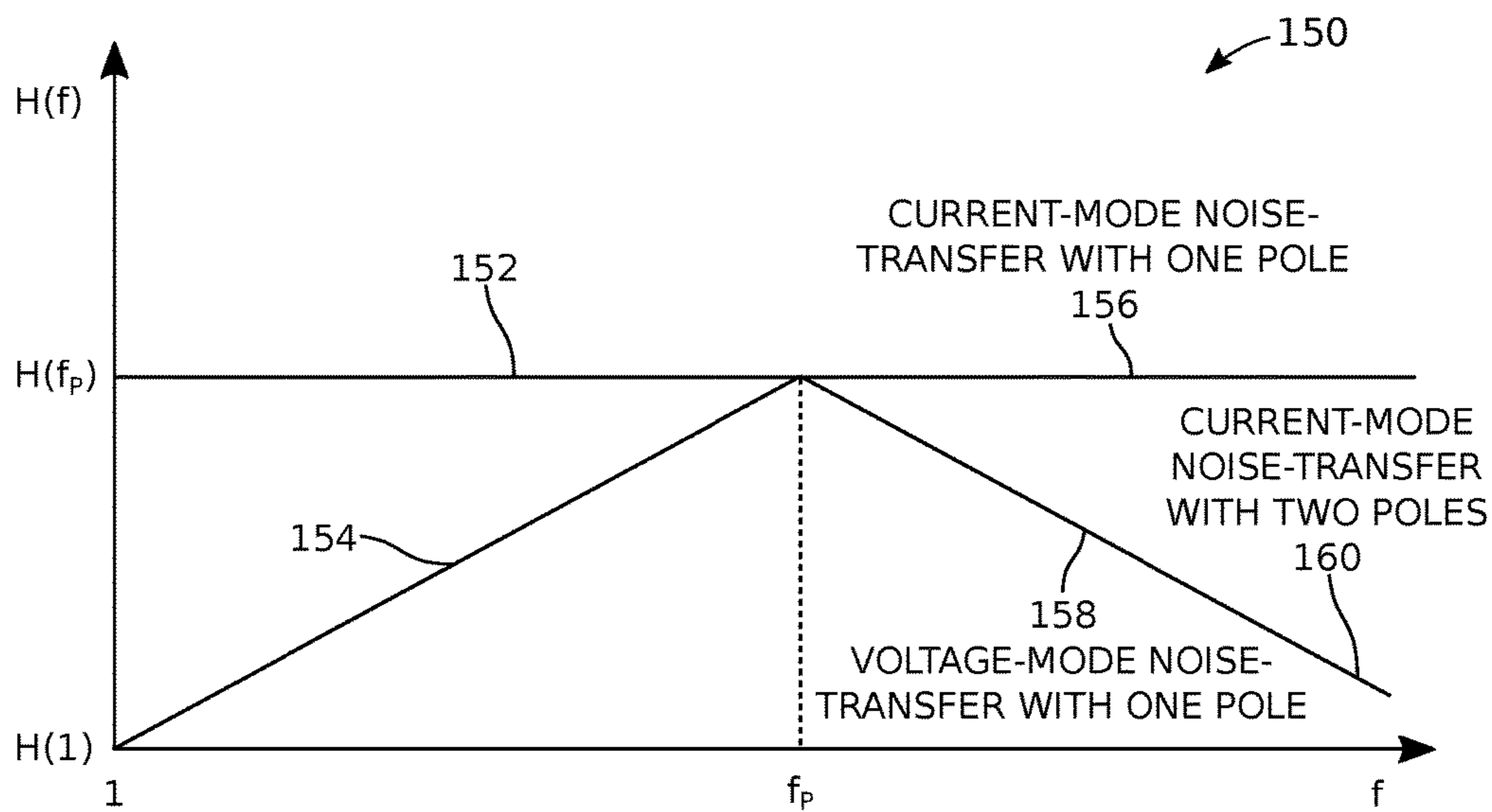


Fig. 8

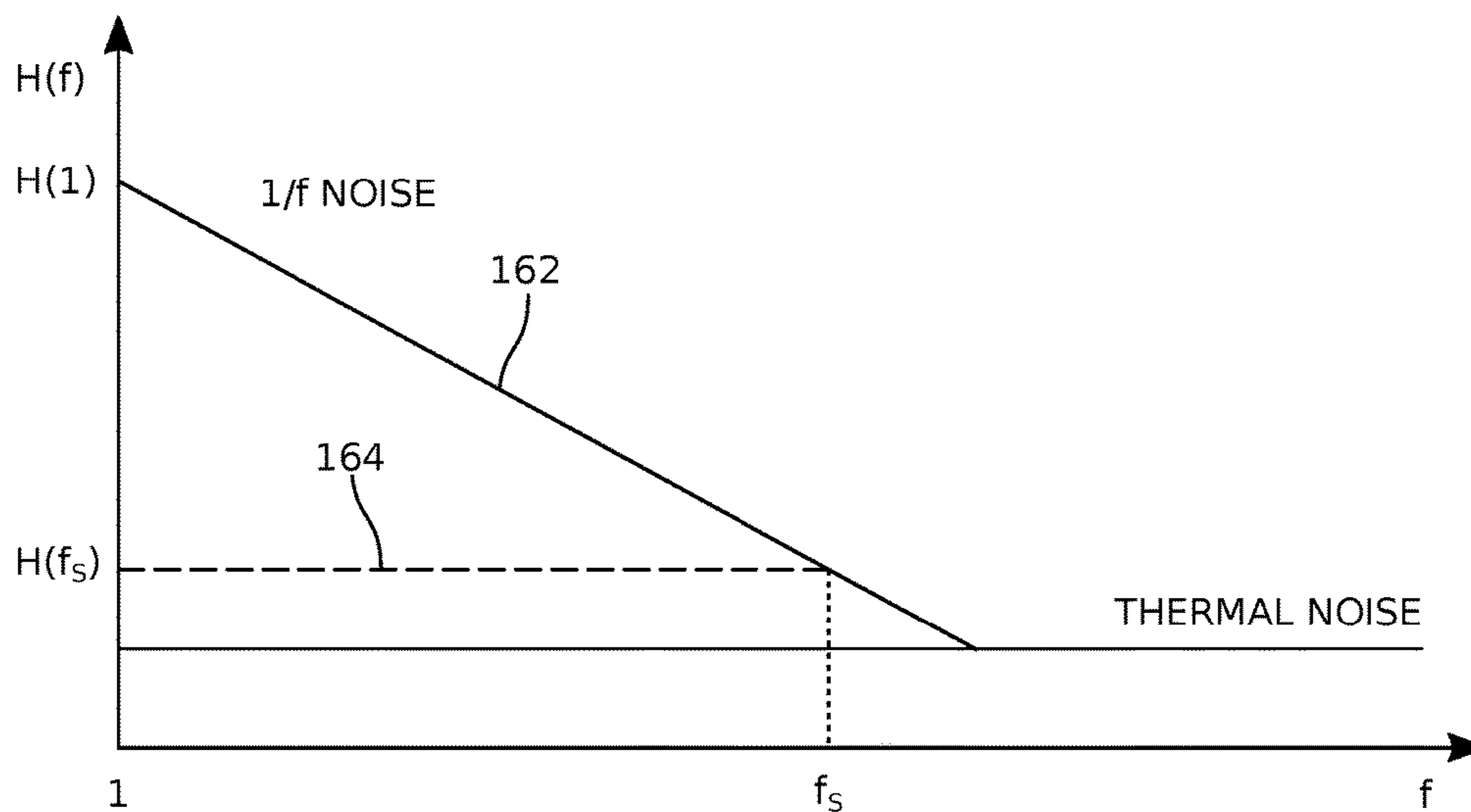


Fig. 9

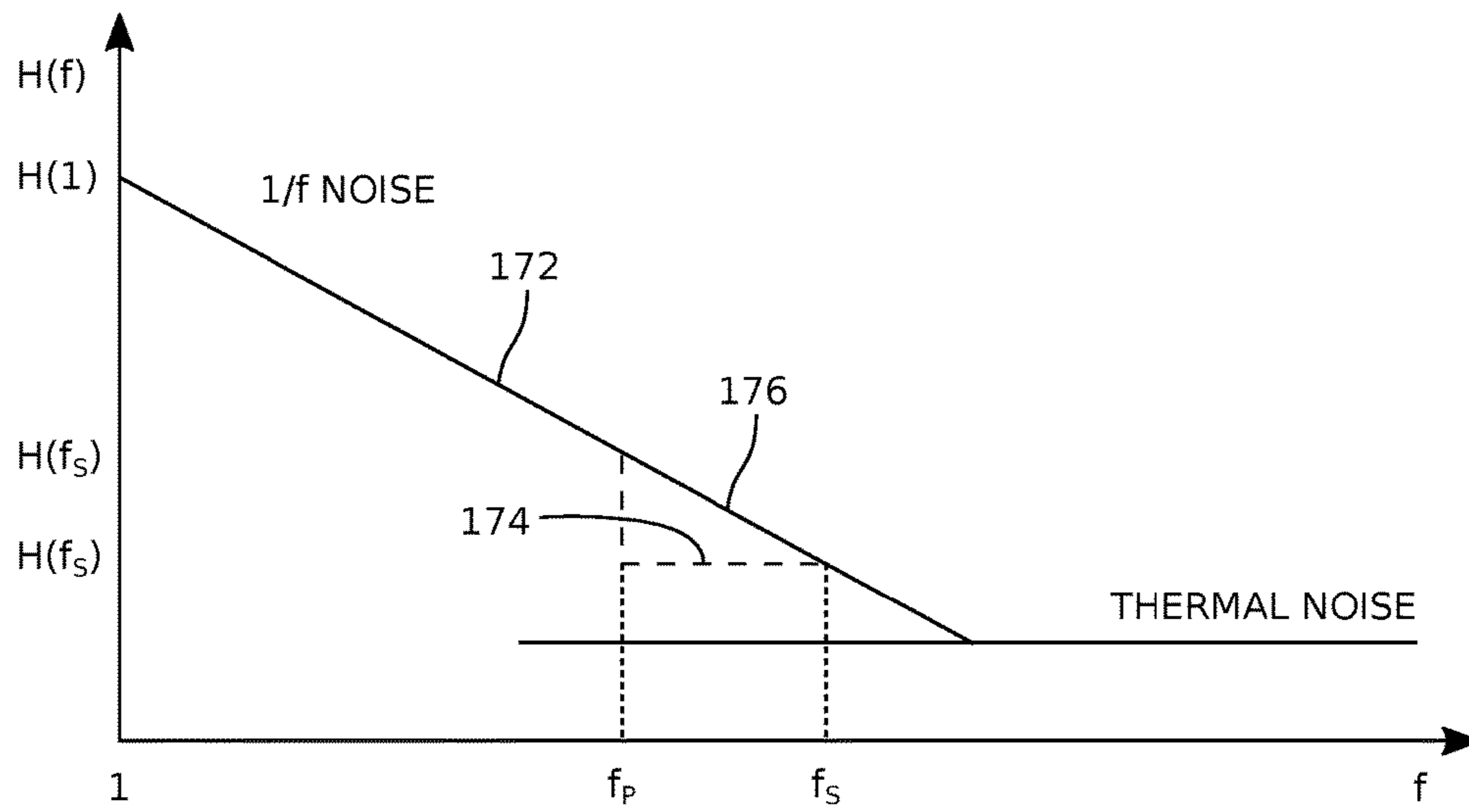


Fig. 10

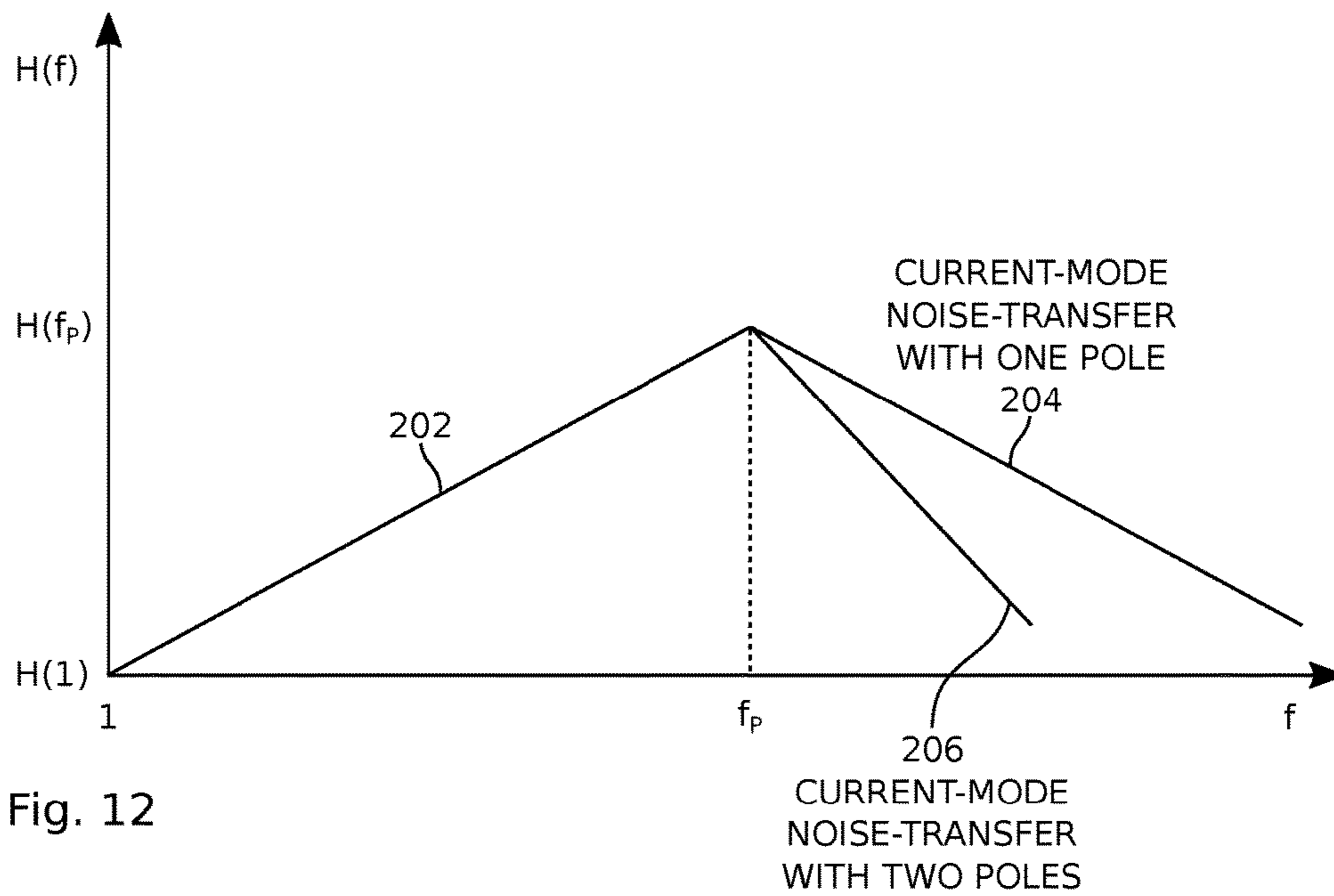


Fig. 12

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SAMPLE-AND-HOLD CIRCUIT WITH ENHANCED NOISE LIMIT

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention generally relates to sample-and-hold circuits, such as those utilized at the front of analog to digital converters and, more particularly, to a sample-and-hold circuit that is current driven at the input and current sensed at the output.

2. Description of the Related Art

Sample-and-hold (S/H) circuits are used to provide discrete signal values, necessary at the input of an analog to digital converter (ADC). One of the most important parameters of a S/H circuit is the amount of thermal noise it generates. This value often determines the necessary resolution, or necessary number of bits required for an ADC. Conventionally, the majority of S/H circuits are voltage-driven at the input and voltage-sensed at the output. For such a circuit its frequency response is a one-pole low-pass filter with pole value at $f=1/(2\pi R_{ON} \cdot C)$, where f is the pole frequency, R_{ON} is the switch on-resistance, and C is the value of a sampling capacitor. If this noise is integrated over the S/H bandwidth, its value is kT/C , where k is the Boltzmann constant and T is the Kelvin temperature.

In recent years this value has been an undisputed limit of S/H thermal noise performance. However, a need has developed to lower the amount of S/H thermal noise in order to limit the number of required ADC bits, which may result in a smaller ADC footprint and its reduced power consumption.

It would be advantageous if a S/H circuit existed having a lowpass signal transfer function and a highpass noise transfer function with the potential of lowering thermal noise below the kT/C value.

SUMMARY OF THE INVENTION

A sample and hold (S/H) circuit is provided herein that is current driven at the input and current sensed at the output. A first capacitor, to ground, is connected at the input to a pair of complementary metal-oxide-semiconductor (CMOS) switches, and a second (optional) capacitor, to ground, is connected to CMOS switch output. Optionally, a single field effect transistor (FET) may be used as the switch. The first capacitor, in cooperation with an input current drive, forms a highpass noise transfer function that substantially reduces the $1/f$ (flicker) noise of the switch(es). The second capacitor helps improve the noise transfer rolls-off further, reducing the overall noise. The overall noise level is significantly lower than a conventional voltage-driven and voltage-sensed sample-and-hold circuit that has a lowpass transfer function and that after integration demonstrates a noise limit of kT/C , where k is the Boltzmann constant, T is the absolute temperature in Kelvin, and C is a value of a sampling capacitor. Depending on the circuit parameters, the sample-and-hold circuit presented herein shows an integrated noise improvement of between 5 and 10 decibels (dB) below the kT/C limit.

Accordingly, a sample-and-hold circuit with an enhanced noise limit is provided. The S/H circuit uses at least a first field effect transistor (FET) having a first source drain (S/D) to accept an analog input signal current (I_S), a second S/D,

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and a gate to accept a binary level first digital control signal. A source resistance (R_S), represented schematically as source resistor (R_S), has a first terminal connected to the first S/D of the first FET and a second terminal connected to ground. A first capacitor (C_1) has a first terminal connected to the first S/D of the first FET and a second terminal connected to ground. As a result, the second S/D of the first FET presents a current-sensed analog output signal (I_O) in response to the first digital control signal enabling the first FET at a first time. In one aspect, a second capacitor has a first terminal connected to the second S/D of the first FET and a second terminal connected to the reference voltage. As mentioned above, in another aspect a complementary second FET has a second S/D connected to the first S/D of the first FET, a first S/D connected to the second S/D of the first FET, and a gate to accept a binary level second digital control signal, complementary to the first digital control signal. The second digital control signal enables the second FET at the first time.

Additional details of the above-described current-mode S/H circuit are presented below.

BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1A and 1B are schematic diagrams of a current-driven, current-sensed sample- and hold-circuit using, respectively, a single FET and complementary switches.

FIG. 2 is a schematic diagram of the S/H current-mode circuit with ideal components supporting the derivation of the signal transfer function.

FIG. 3 is a schematic diagram of the S/H current-mode circuit with ideal components supporting the derivation of the noise transfer function.

FIG. 4 is a schematic diagram of a voltage-mode sample and hold test-bench circuit.

FIG. 5 is a schematic diagram of the voltage-sensed circuit driven by a signal current source.

FIG. 6 is a schematic diagram of the voltage-sensed, current-driven circuit supporting the derivation of a voltage transfer function.

FIG. 7 is a schematic diagram of the voltage-sensed, current-driven circuit supporting the derivation of a noise transfer function.

FIG. 8 is a graph contrasting two noise transfer functions.

FIG. 9 is a first graph showing two principles of $1/f$ noise handling.

FIG. 10 is a second graph showing two principles of $1/f$ noise handling.

FIG. 11 is the schematic diagram of FIG. 2 featuring the addition of a second capacitor for steeper noise roll-off.

FIG. 12 is a graph depicting two noise transfer functions for the current-sensed, current-driven S/H circuit.

DETAILED DESCRIPTION

FIGS. 1A and 1B are schematic diagrams of a current-driven, current-sensed sample and hold circuit using, respectively, a single FET and complementary switches. The sample-and-hold (S/H) circuit 10 uses a switch enabled with a single field effect transistor (FET) 11, as shown in FIG. 1A, or enabled with a pair of complementary switches 12 (e.g., FETs such as complementary metal-oxide-semiconductor CMOS transistors), as shown in FIG. 1B. The switch or switches are connected to the input capacitor C_1 14 through their input source/drain (S/D) terminals. The complementary switch 12 does not change the noise performance, but it substantially improves the linearity. Switch 11 or 12 is

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excited by an input analog signal current source **16** with a source resistance (Rs), represented as source resistor R_S **18**, between the FET (FIG. 1A) or FETS (FIG. 1B) and ground.

Furthermore, the gate of switch **11** (FIG. 1A) is pulsed with binary value digital voltage source V_P **20**, and the gates of switch **12** (FIG. 1B) are pulsed by two complementary digital voltage sources V_P and V_{P_BAR} denoted, respectively, by reference designators **20** and **22**. The digital voltage source enables the switch(es) to selectively pass current or prevent current flow. The output current I_O on line **24** is on the other side of the switch **11** (FIG. 1A) or switches **12** (FIG. 1B), away from the C_1 capacitor **14**.

FIG. 2 is a schematic diagram of the S/H current-mode circuit with ideal components supporting the derivation of the signal transfer function. The model **30** consists of 4 elements only. The transconductance of the FET in FIG. 1A or the complementary switches in FIG. 1B is denoted by g_m and is identified by reference designator **32**. Capacitance C_1 is identified by reference designator **34**, and a signal source I_S with a signal source resistance (Rs), represented schematically as input or source resistor R_S , are respectively identified by the reference designators **36** and **38**. Finally, the output current I_O is identified with the reference designator **40** and it is taken on the opposite side of the transistor(s) from capacitor **34**.

The current signal transfer function of the current-mode S/H of FIGS. 1A and 1B is $I_O/I_S = g_m/(g_m + sC_1)$, which is a first-order lowpass function.

$$\begin{aligned} I_S &= I_{R_S} + I_{C_1} + I_{g_m} \\ &= V_S * (1/R_S + g_m + sC_1) \\ &= (I_O/g_m) * (1/R_S + g_m + sC_1) \\ I_O/I_S &= g_m / (1/R_S + g_m + sC_1) \\ \text{If } 1/R_S \ll g_m &= > I_{R_S} \approx 0 \\ I_O/I_S &= g_m / (g_m + sC_1) \end{aligned}$$

where C_1 is the capacitance value of C_1 ; and, where Rs is the resistance value of Rs.

FIG. 3 is a schematic diagram of the S/H current-mode circuit with ideal components supporting the derivation of the noise transfer function. The model **50** comprises the transconductance of the FET (FIG. 1A) or the complementary switches (FIG. 1B), denoted by g_m and identified by the reference designator **60**. A switch noise current source is denoted by I_{n,g_m} and identified by reference designator **62**. Capacitance C_1 is identified by reference designator **52**, and the signal source I_S with the source resistance (Rs), as represented schematically by source resistor R_S , are respectively identified by the reference designators **54** and **56**. The voltage V_S at the current input of the transistors is identified with reference designators **58**. Finally, the output current I_O is identified with reference designator **64** and it is taken on the opposite (current-sensed) side of switch(es) from capacitor **52**.

The current noise transfer function of the S/H circuit is $I_O/I_{n,g_m} = sC_1/(g_m + sC_1)$, which is a first-order highpass function. The combined transfer function that uses noise transfer in combination with signal transfer is calculated to be $(I_O/I_{n,g_m}) * (I_O/I_S) = sC_1/(g_m + sC_1) * g_m/(g_m + sC_1) = sC_1/g_m / (g_m + sC_1)^2$. This function has a zero at dc—(zero Hertz) and a double pole at g_m/C_1 . As it is shown in FIG. 8, one pole compensates for zero and the transfer is flat after pole

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frequency g_m/C_1 . However, second pole gives the transfer a desired drop-off after the double-pole frequency g_m/C_1 .

$$\begin{aligned} I_O &= I_{n,R_S} + I_{R_S} + I_{C_1} - I_{n,g_m} + I_{g_m} \\ &= I_{n,R_S} - I_{n,g_m} + V_S * (1/R_S + g_m + sC_1) \end{aligned}$$

$$\text{If } 1/R_S \ll g_m = > I_{n,R_S} + I_{R_S} \approx 0$$

Also, at high frequency $I_O \approx I_{C_1}$

$$\text{and } I_{n,g_m} \approx I_{g_m} + I_{C_1}$$

$$\begin{aligned} I_O/I_n &= I_{C_1} / (I_{g_m} + I_{C_1}) \\ &= V_S * sC_1 / (g_m + sC_1) * V_S \\ &= sC_1 / (g_m + sC_1) \end{aligned}$$

Combined noise transfer function:

$$\begin{aligned} (I_O/I_{n,g_m}) * (I_O/I_S) &= sC_1 / (g_m + sC_1) * g_m / (g_m + sC_1) \\ &= sC_1 * g_m / (g_m + sC_1)^2 \end{aligned}$$

FIG. 4 is a schematic diagram of a voltage-mode sample and hold test-bench circuit. The voltage-mode S/H circuit **70** includes a single switch **M1**, as shown here in the interest of simplicity, but may alternatively be a pair of complementary switches such as shown in FIG. 1B. **M1** is identified by reference designator **76** and is connected to an output capacitor C_1 **74**. Switch **76** is excited by an input analog signal voltage source **82** with a source resistance (Rs), represented schematically by source resistor R_S **80**. Additionally, the switch **76** is pulsed from a digital voltage source **84**. Two voltages are present in this circuit: the input voltage V_S **82** and the output voltage V_O **72**. The derivation of transfer functions is easier if the voltage signal source **82** is replaced a current source, as described in the explanation of FIG. 5 below.

FIG. 5 is a schematic diagram of the voltage-sensed circuit driven by a signal current source. The voltage-mode S/H circuit **90** of FIG. 5 is derived from the circuit of FIG. 4. It includes a single switch **M1** **96** that is connected to an output capacitor C_1 **94**. Switch **96** is excited by an input analog signal current source **100** with a source resistance (Rs), represented schematically by source resistor R_S **102**. Additionally, the switch **96** is pulsed from a digital voltage source **104**. Two voltages are present in this circuit: the input voltage V_S **98** and the output voltage V_O **92**.

FIG. 6 is a schematic diagram of the voltage-sensed, current-driven circuit supporting the derivation of a voltage transfer function. The model **110** comprises 4 elements only. The transconductance of the switch **96** is denoted by g_m and identified with reference designator **116**. The model **110** also comprises capacitance C_1 **114**, signal source I_S **120**, and source resistance (Rs), represented schematically by source resistor R_S **122**. Finally, the output voltage V_O **112** and it is taken on the opposite side of the switch from capacitor **114**. Additionally, the input voltage V_S is identified with reference designator **118**.

The voltage signal transfer function of the voltage-mode S/H is $V_O/V_S = g_m/(g_m + sC_1)$, which is a first-order lowpass function.

$$\begin{aligned} I_S + I_{R_S} &= I_{g_m} \\ I_S + V_S/R_S &= (V_S - V_O) * g_m \end{aligned}$$

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-continued

$$I_S = V_S * (1/R_S + g_m) - V_O * g_m$$

$$\text{If } 1/R_S \ll g_m = > I_{R_S} \approx 0$$

$$I_{C_1} = V_O * sC_1 = I_S$$

$$I_S = V_S * g_m - (I_S / sC_1) * g_m$$

$$I_S + (I_S / sC_1) * g_m = V_S * g_m$$

$$I_S * (1 + g_m / sC_1) = V_S * g_m$$

$$V_O * sC_1 * (1 + g_m / sC_1) = V_S * g_m$$

$$V_O / V_S = g_m / (g_m + sC_1)$$

FIG. 7 is a schematic diagram of the voltage-sensed, current-driven circuit supporting the derivation of a noise transfer function. The model **130** comprises switch transconductance **136**, denoted by g_m , a switch noise current source **144** denoted by I_n, g_m , capacitance C_1 **134**, a signal current source I_S **140**, and source resistance (R_S), represented schematically by source resistor R_S **142**. The voltage V_S at the input to the switch is identified with reference designator **138**. Finally, the output voltage V_O **132** is taken from the same side of a switch as capacitor **134**.

The voltage noise transfer function of the voltage-mode S/H is $V_O / V_{n, gm} = g_m / (g_m + sC_1)$, which is a first-order low-pass function.

$$I_{n, R_S} + I_{R_S} = I_{n, gm} + I_{gm}$$

$$\text{If } 1/R_S \ll g_m = > I_{n, R_S} + I_{R_S} \approx 0$$

$$I_{C_1} = I_{n, gm} - I_{gm}$$

$$I_{C_1} = V_O * sC_1$$

$$V_O * sC_1 = I_{n, gm} - V_O * g_m$$

$$I_{n, gm} = V_O * (g_m + sC_1)$$

$$I_{n, gm} = V_{n, gm} * g_m$$

$$V_{n, gm} * g_m = V_O * (g_m + sC_1)$$

$$V_O / V_{n, gm} = g_m / (g_m + sC_1)$$

FIG. 8 is a graph contrasting two noise transfer functions. The lowpass graph (sections **152** and **158**) is associated with a voltage-mode circuit. It is flat until the pole frequency of f_p . Then it rolls-off due to its pole. A highpass graph is associated with a current-mode circuit. Its response **154** increases until the pole frequency of f_p . Then it flattens due to its pole (section **156**). Practically, however, two poles are present at f_p . Therefore, the current-mode noise transfer **160** rolls-off similarly to the voltage-mode circuit (section **158**).

For a voltage-driven circuit both transfer functions for signal and noise are the same:

$$V_O / V_S = g_m / (g_m + sC_1) \quad V_O / V_{n, gm} = g_m / (g_m + sC_1)$$

In order to calculate the total thermal noise contribution certain assumptions need to be made:

1) We calculate only the $1/2$ of the total bandwidth, exactly to the pole position and not beyond to be comparable with the current-driven circuit that takes the same bandwidth.

2. We use an approximation that $1/R_S \ll g_m$, which results in much simpler transfer function. Hence:

$$(V_O / V_{n, gm})^2 = |H(j\omega)|^2 = |g_m^2 / (g_m^2 + \omega^2 C^2)| = 1 / (1 + \omega^2 C^2 / g_m^2)$$

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In order to calculate the bandwidth, we need to integrate $|H(j\omega)|^2$ from 0 to 1. 1 corresponds to $\omega_p = g_m / C$, which is the pole frequency.

$$\int_0^1 d\omega / (1 + \omega^2 C^2 / g_m^2) = g_m / C \int_0^1 dx / (1 + x^2) = (g_m / C) * \arctan|_0^1 = (g_m / C) * (\pi/4 - 0) = (g_m / C) * (\pi/4)$$

Hence:

$$\begin{aligned} V^2(f)_{noise} &= 4kT * (1/g_m) * BW(\omega) * (1/2\pi) = 4kT * (1/g_m) * (g_m / C) * (\pi/4) * (1/2\pi) \\ &= 4kT * (1/C) * (1/8) = kT/2C. \end{aligned}$$

This can be further converted to: $kT/2C = (kT\omega) / (2g_m)$.

For the current-driven circuits of FIG. 1A or 1B, the transfer function for signal is LP (lowpass) and the transfer function for noise is HP (highpass):

$$I_O / I_S = g_m / (g_m + sC_1) \quad I_O / I_n = s g_m C_1 / (g_m + sC_1)$$

In order to calculate the total thermal noise contribution certain assumptions need to be made:

3) We calculate only the $1/2$ of the total bandwidth, exactly to the pole position and not beyond to be comparable with the voltage-sensed circuit that takes the same bandwidth.

4) We use the approximation that $1/R_S \ll g_m$, which results in much simpler transfer function.

5) The combined transfer function for noise has the equation:

$$s g_m C / (g_m + sC)^2.$$

Hence:

$$\begin{aligned} |H(j\omega)|^2 &= |(\omega C)^2 g_m^2 / (g_m^2 + \omega^2 C^2)^2| = [(\omega C)^2 (g_m^2 / g_m^4)] / [(1 + \omega^2 C^2 / g_m^2)^2] \\ &= (C^2 / g_m^2) * (\omega)^2 / [(1 + \omega^2 C^2 / g_m^2)^2] \end{aligned}$$

In order to calculate the bandwidth, we need to integrate $|H(j\omega)|^2$ from 0 to 1. 1 corresponds to $\omega_p = g_m / C$, which is the pole frequency.

$$\begin{aligned} (C^2 / g_m^2) * \int_0^1 \omega^2 d\omega / [(1 + \omega^2 C^2 / g_m^2)^2] &= g_m / C (C^2 / g_m^2) (g_m^2 / C^2) \int_0^1 x^2 dx / (1 + x^2)^2 \\ &= (g_m / C) * \{1/2[-x / (1 + x^2) + \arctan(x)]\}_0^1 \\ &= (g_m / C) * [1/2((-1 / (1 + 1) + \pi/4 - 0))] \\ &= (g_m / C) * (\pi/8 - 1/4). \end{aligned}$$

Hence,

$$\begin{aligned} I^2(f)_{noise} &= 4kT * g_m * BW(\omega) * (1/2\pi) \\ &= 4kT * g_m * (g_m / C) * (\pi/8 - 1/4) * (\pi/2) * (1/2\pi) \\ &= 0.1427 * kT / C * \omega^2. \end{aligned}$$

This can be further converted to: $0.1427 * kT / C * \omega^2 = 0.1427 * kT * \omega * g_m$.

In order to compare the noise performance for both circuits, the total thermal noise contributions are divided:

$$\text{Voltage-driven circuit: } V^2(f)_{noise} = (kT\omega)/(2g_m).$$

This can be converted into current:

$$I^2(f)_{noise} = kT\omega * g_m/2.$$

$$\text{Current-driven circuit: } I^2(f)_{noise} = 0.1427 * kT\omega * g_m.$$

Hence, the improvement can be calculated as a ratio:

$$(kT\omega * g_m/2)/0.1427 * kT\omega * g_m = 0.5/0.1427 = 3.5,$$

$$\text{or in dBs: } 10 \log_{10}(3.5) = 5.445 \text{ dB} \approx 5.4 \text{ dB}.$$

In some aspects the total noise improvement may reach 10 dB or more. This can be explained as follows. Practical modern MOS devices have a significant 1/f noise contribution. In current deep-submicron CMOS technologies the 1/f noise corner can be anywhere from 10 MHz to 100 MHz.

FIG. 9 is a first graph showing two principles of 1/f noise handling. The solid line **162** is associated with a voltage-mode circuit that integrates 1/f (flicker) noise until the sampling frequency of f_S . The result of this integration is $b^2/3$, where $b^2 = H(1)^2$. The dashed line **164** is associated with a current-mode circuit. Because of its highpass noise transfer it integrates a flat spectrum until f_S . The result of this integration is b^2/f_S . The ratio of these two integrations gives a 1/f noise improvement of current-mode over voltage-mode circuitry, which is calculated to be $f_S/3$.

Referring to FIGS. 8 and 9, it can be seen that with a voltage-driven circuit provides no help for the suppression of 1/f noise. This is a result of lowpass (LP) noise characteristics that pass all 1/f noise to the output. This can be represented graphically (see the FIGS. 8 and 9), or numerically as follows.

$$|I_1(f)|^2 = a^2/(f^2) [1 + (2\pi)^2 f^2 C_1^2 / g_m^2] \approx a^2/(f^2) \text{ for } f < g_m / (2\pi C_1)$$

For an ideal current-driven circuit with zero at the origin the 1/f noise is flattened, meaning there is no high noise value at $f=0$, and then a linear drop-off until the 1/f corner.

$$|I_2(f)|^2 = a^2/BW^2 \text{ for } f < g_m / (2\pi C_1)$$

The spectrum starts from zero Hertz and it is flat. Hence, after integration the residuum 1/f noise looks like a thermal noise.

Calculating the integrals in both cases, $BW=10$ MHz and $BW < g_m / (2\pi C_1)$.

Voltage Case:

$$S_1^2(f) = a^2 * \int_1^{BW} (df/f^2) * (C^2/g_m^2) * (2\pi f)^2 / [(1 + (2\pi f)^2 C^2 / g_m^2)^2]$$

$$[1 - 1/(BW)^3] \approx a^2/3, \text{ where}$$

$$a^2 = 1/f \text{ noise power value for } f=1 \text{ Hz, or } |I_1(1)|^2 = a^2$$

Current Case:

$$S_2^2(f) = a^2 * \int_1^{BW} (df/f^2) * (C^2/g_m^2) * (2\pi f)^2 / [(1 + (2\pi f)^2 C^2 / g_m^2)^2]$$

$$\approx a^2 \int_1^{BW} C^2 / g_m^2 (2\pi)^2 df$$

$$= (a^2 / BW^2) * f |_1^{BW} = (a^2 / BW^2) * [BW - 1]$$

$$\approx (a^2 / BW^2) * BW = a^2 / BW$$

$$S_1^2(f) / S_2^2(f) = (1/3) * BW = 3.33 * 10^6, \text{ or}$$

$$10 \log_{10}(3.33 * 10^6) \approx 65.2 \text{ dB}$$

Theoretically, the total 1/f noise improvement is 65 dB. However, this result is not always practical.

FIG. 10 is a second graph showing two principles of 1/f noise handling. The solid line **172** is associated with a voltage-mode circuit, which integrates 1/f noise until the sampling frequency of f_S . Between a corner frequency f_P and sampling frequency f_S , the graph portion is identified by the numeral **176** and is still of 1/f type. A flat spectrum identified by the numeral **174** is associated with a current-mode circuit. Due to the highpass (HP) characteristics of the current-mode circuit, from a corner frequency f_P to a sampling frequency f_S , the dashed-line graph portion identified by reference designator **174** is flat. That is, to compare the two circuits an intermediate frequency point f_P is taken into account. At this frequency the current-mode circuit regains its highpass noise transfer function. As a result, between f_P and f_S , the voltage-mode circuit integration noise is $c^2/3$, where $c^2 = H(f_P)^2$, and a current-mode circuit integration noise **174** is $c^2/(f_S - f_P)$. The ratio of these two integrals gives the 1/f noise improvement of current-mode over voltage-mode circuitry. In this case, it is calculated to be $(f_P - f_S)/3$.

For simplicity, an assumption that $1/R_S \ll g_m$ is used. If this assumption is not used the current-mode noise transfer is not highpass at dc (zero Hertz), but it is flat and then becomes highpass from a certain frequency. For example, if this corner is at 1 megahertz (MHz), then for first 1 MHz the current-driven circuit behaves like a voltage-driven circuit. But at 1 MHz the HP behavior starts and for next 1 decade until 10 MHz, the 1/f noise remains flat. The perceived advantage is around 4.8 dB.

$$S_3^2(f) = (b^2/3) [1 - 1/(10-1)^3] = (b^2/3) [1 - 1/9^3]$$

$$\approx b^2/3 \text{ for voltage-mode circuit.}$$

$$S_4^2(f) = b^2/(10-1) = b^2/9 \text{ for current-mode circuit.}$$

$$S_3^2(f) / S_4^2(f) = (b^2/3) / (b^2/9) = 3, \text{ or } 10 \log_{10}(3) \approx 4.8 \text{ dB, see FIG. 10.}$$

So, the total improvement should be around 5.4 dB for a flat thermal noise and 4.8 dB for 1/f noise, totaling 10.2 dB.

FIG. 11 is the schematic diagram of FIG. 2 featuring the addition of a second capacitor for steeper noise roll-off. The model **180** includes output current I_O **182**, output capacitor C_2 **184**, the output voltage V_O on line **186**, switch transconductance **196**, input resistance (R_S), represented schematically as resistor R_S **194**, input current source I_S **192**, source voltage V_S **190**, output resistance (R_O), represented schematically as resistor R_O **198**, and input capacitor C_1 **188**.

$$V_O = -R_O * I_O, I_S = I_{R_S} + I_{C_1} + I_{g_m} = V_S * (1/R_S + g_m + sC_1) -$$

$$V_O * g_m - I_O$$

$$= I_{C_2} + I_{g_m} = V_O * (sC_2 + g_m) - V_S * g_m$$

$$= R_O * I_O * (sC_2 + g_m) - V_S * g_m$$

$$I_S = V_S * (1/R_S + g_m + sC_1) + R_O * I_O * g_m = > V_S$$

$$= I_O * [R_O(sC_2 + g_m) + 1] / g_m$$

where R_O represents the resistance value of R_O ; and, where C_2 represents the capacitance value of C_2 .

$$\begin{aligned}
I_S &= \{I_O * [R_O(sC_2 + g_m) + 1] / g_m\} * (1 / R_S + g_m + sC_1) + R_O * I_O * g_m \\
&= (I_O / g_m) * [R_O(sC_2 + g_m) + 1] * (1 / R_S + sC_1) + (I_O / g_m) * \\
&\quad [R_O(sC_2 + g_m) + 1] * g_m + R_O * I_O * g_m \\
&= (I_O / g_m) * [R_O(sC_2 + g_m) + 1] * (1 / R_S + sC_1) + I_O * (sR_O C_2 + 1) = \\
&\quad (I_O / g_m) * [sC_2 R_O / R_S + g_m R_O / R_S + 1 / R_S + s^2 R_O C_1 C_2 + \\
&\quad s g_m R_O C_1 + s C_1] + I_O / g_m * (s g_m R_O C_2 + g_m)
\end{aligned}$$

$$\begin{aligned}
I_O / I_S &= g_m / [(sC_2 R_O / R_S + g_m R_O / R_S + 1 / R_S + s^2 R_O C_1 C_2 + \\
&\quad s g_m R_O C_1 + s C_1) + (s R_O C_2 + 1)] \\
&= g_m / [s^2 R_O C_1 C_2 + s(C_2 R_O / R_S + g_m R_O C_1 + C_1 + g_m R_O C_2) + \\
&\quad g_m R_O / R_S + 1 / R_S + g_m]
\end{aligned}$$

Since R_O is high, then $g_m * R_O \gg 1$. In some aspects

$$g_m * R_O > 10 \text{ hence,}$$

$$\begin{aligned}
I_O / I_S &\approx g_m / [s^2 R_O C_1 C_2 + s g_m R_O (C_1 + C_2) + g_m R_O / R_S] \\
&= (g_m / R_O C_1 C_2) / [s^2 + s g_m (C_1 + C_2) / C_1 C_2 + g_m / R_S C_1 C_2]
\end{aligned}$$

$$\omega_O^2 = g_m / R_S C_1 C_2,$$

$$\begin{aligned}
\omega_O / Q &= g_m (C_1 + C_2) / C_1 C_2 \sqrt{(g_m / R_S C_1 C_2) / O} \\
&= g_m (C_1 + C_2) / C_1 C_2
\end{aligned}$$

$$Q = \sqrt{(g_m / R_S C_1 C_2) / g_m (C_1 + C_2) / C_1 C_2} = \sqrt{(C_1 C_2 / g_m R_S) / (C_1 + C_2)}$$

$$Q = C / 2C = 0.5, g_m \approx R_S, \omega_O = 1m / 10p = 1 * 10^8 = > f_O = 15.9 \text{ MHz.}$$

FIG. 12 is a graph depicting two noise transfer functions for the current-sensed, current-driven S/H circuit. The high-pass portion **202** increases until the pole frequency of f_p . Then it rolls-off due to its poles. Two cases are possible. One is when only one input capacitor C_1 is present, with one real pole **204**. In the second case two capacitors, the input C_1 and the output C_2 , are present, with two complex poles **206**. Thus, with the second capacitor the HP transfer has not one-real pole, but two complex poles giving it a preferred steeper -40 dB per decade roll-off, instead of 20 dB per decade a roll-off.

It should be noted that for $g_m \approx R_S$ and for $C_1 = C_2$ the $Q = 0.5$ is low. The system is critically damped. It demonstrates no overshoot and fast response. However, even with such a low Q the roll-off is 40 dB per decade and not 20 dB per decade as in the case of a system with one capacitor. The noise improvement can be calculated as follows:

For a one pole roll-off with $f_p = 10$ MHz, the integrated noise from 10 MHz to 100 MHz is:

$$\begin{aligned}
(I_O / I_{n,gm})^2 &= |1 / (1 + \omega^2 C^2 / g_m^2)| \\
&= |1 / (1 + (2\pi)^2 f^2 C^2 / g_m^2)| \approx (2\pi)^2 * (C / g_m)^2 / f^2
\end{aligned}$$

$$\begin{aligned}
S_5^2(f) &= \int_{10 * f_p}^{f_p} (2\pi)^2 * (C / g_m)^2 * df / f^2 \\
&= (1/3) * (1/2\pi) * (g_m / C) / f^3 \Big|_{f_p * 10}^{f_p} \\
&= (1/3) * (1/2\pi) * (g_m / C) * (1 - 1 / (10 - 1)^2) \\
&\approx (1/3) * f_p
\end{aligned}$$

-continued

$$\begin{aligned}
S_6^2(f) &= \int_{10 * f_p}^{f_p} (2\pi)^2 * (C / g_m)^2 * df / f^4 = (1/5) * (1/2\pi) * \\
&\quad (g_m / C) / f^5 \Big|_{f_p * 10}^{f_p} \\
&= (1/5) * (1/2\pi) * (g_m / C) * (1 - 1 / (10 - 1)^4) \\
&\approx (1/5) * f_p
\end{aligned}$$

$$S_5^2(f) / S_6^2(f) = (1/3) * f_p / (1/5) * f_p = 5/3 = > 10 * \log_{10}(5/3) = 2.2 \text{ dB.}$$

In summary, the current-mode S/H circuit performance can be summarized as follows:

1. The total thermal noise improvement is 5.4 dB, if we just drive and sense the circuit with current instead of voltage.

2. Much more performance gain is achieved when a true $1/f$ noise characteristic for the switches is considered. Because the current-mode circuit has a HP noise transfer, it cancels $1/f$ noise low frequency component. If the HP starts at dc the noise improvement may reach 65 dB or more.

3. However, in practical circuits it is expected that the HP starts not at dc-, but at higher frequency, so that the low end is not compensated. However, some performance improvement due to $1/f$ noise cancellation always exists. For a just a decade of HP noise transfer function, another 4.8 dB is gained. Then the total circuit noise improvement (thermal and $1/f$) is close to 10.2 dB.

4. Finally, adding second capacitor— C_2 in the current-mode circuit results in a faster roll-off. The noise improvements depend on the circuit parameters, but for a typical case they are calculated to be 2.2 dB. Hence, the total circuit noise improvement may reach 12.4 dB.

5. In some aspects the current-mode circuit may have as much as 10 dB lower noise as compared to a voltage-mode, which is well within the reach due to a 2 dB margin.

A current-mode S/H circuit has been presented. Modification of the circuit may become apparent in those of ordinary skill in the art upon reading the present disclosure, and it is intended that the scope of the invention disclosed herein be limited only by the broadest interpretation of the appended claims to which the inventor is legally entitled.

I claim:

1. A sample-and-hold circuit with an enhanced noise limit, the sample-and-hold circuit comprising:

a first field effect transistor (FET) having a first source drain (S/D) to accept an analog input signal current (I_S), a second S/D, and a gate to accept a binary level first digital control signal;

second FET having a second S/D connected to the first S/D of the first FET, a first S/D connected to the second S/D of the first FET, and a gate to accept a binary level second digital control signal, complementary to the first digital control signal;

a source resistance (R_S) between the first S/D of the first FET and ground;

a first capacitor (C_1) having a first terminal connected to the first S/D of the first FET, and a second terminal connected to ground; and,

wherein the second S/D of the first FET presents a current-sensed analog output signal (I_O) in response to the first and second digital control signals respectively enabling the first and second FETs at a first time.

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2. The sample-and-hold circuit of claim 1 wherein the combination of the first FET, second FET, source resistance, and first capacitor create a lowpass current signal transfer function.

3. The sample-and-hold circuit of claim 2 wherein the lowpass current signal transfer function is represented as follows:

$$I_O/I_S = g_m / (g_m + sC_1);$$

where s is a complex frequency= $j\omega$;

where j is an imaginary unit;

where $\omega = 2 \cdot \pi \cdot$ frequency;

where C_1 represents the capacitance value of C_1 ; and,

where g_m is the transconductance of the first and second FETs.

4. The sample-and-hold circuit of claim 3 wherein the combination of the first FET, second FET, source resistance, and first capacitor create a highpass noise transfer function.

5. The sample-and-hold circuit of claim 4 wherein the highpass noise transfer function is represented as follows:

$$(I_O/I_{n,gm}) = s g_m C_1 / (g_m + s C_1); \text{ and,}$$

where $I_{n,gm}$ is a switch noise current source associated with the first and second FETs.

6. The sample-and-hold circuit of claim 5 wherein a combined noise transfer function, derived from the lowpass current transfer function (I_O/I_S) and highpass noise transfer function ($I_O/I_{n,gm}$) is represented as follows:

$$(I_O/I_{n,gm}) \cdot (I_O/I_S) = s g_m C_1 / (g_m + s C_1)^2.$$

7. The sample-and-hold circuit of claim 6 wherein the combination of the first FET, second FET, source resistance, and first capacitor create a flat spectrum flicker ($1/f$) noise response from the first and second FET corner frequency (f_P) to a sampling frequency (f_S), when $1/R_S$ is at least an order of magnitude less than g_m .

8. The sample-and-hold circuit of claim 6 wherein the combination of the first FET, second FET, source resistance, and first capacitor create a flat thermal noise ($(I(f)_{noise})$) response from the first and second FET corner frequency (f_P) to a sampling frequency (f_S), when $1/R_S$ is at least an order of magnitude less than g_m .

9. The sample-and-hold circuit of claim 8 wherein

$$P^2(f)_{noise} = 0.1427 \cdot kT \cdot g_m;$$

where k is the Boltzmann constant; and,

where T is the Kelvin temperature.

10. The sample-and-hold circuit of claim 1 further comprising:

a second capacitor (C_2) having a first terminal connected to the second S/D of the first FET and a second terminal connected to ground.

11. The sample-and-hold circuit of claim 10 further comprising:

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an output resistance (R_O) between the second S/D of the first FET and ground;

wherein the combination of the first FET, second FET, source resistance, output resistance, first capacitor, and second capacitor create a lowpass current signal transfer function represented as follows:

$$I_O/I_S = (g_m/R_O C_1 C_2) / [s^2 + s g_m (C_1 + C_2) / C_1 C_2 + g_m/R_S C_1 C_2], \text{ where } g_m \cdot R_O \text{ is at least greater than } 10;$$

where s is a complex frequency= $j\omega$;

where j is an imaginary unit;

where $\omega = 2 \cdot \pi \cdot$ frequency;

where C_1 represents the capacitance value of C_1 ;

where C_2 represents the capacitance value of C_2 ; and,

where g_m is the transconductance of the first and second FETs.

12. A sample-and-hold circuit with an enhanced noise limit, the sample-and-hold circuit comprising:

at least a first field effect transistor (FET) having a first source drain (S/D) to accept an analog input signal current (I_S), a second S/D, and a gate to accept a binary level first digital control signal;

a source resistance (R_S) between the first S/D of the first FET and ground;

a first capacitor (C_1) having a first terminal connected to the first S/D of the first FET and a second terminal connected to ground;

a second capacitor having a first terminal connected to the second S/D of the first FET and a second terminal connected to ground; and,

wherein the second S/D of the first FET presents a current-sensed analog output signal (I_O) in response to the first digital control signal enabling the first FET at a first time.

13. The sample-and-hold circuit of claim 12 further comprising:

an output resistance (R_O) between the second S/D of the first FET and ground;

wherein the combination of the first FET, source resistance, output resistance, first capacitor, and second capacitor create a lowpass current signal transfer function represented as follows:

$$I_O/I_S = (g_m/R_O C_1 C_2) / [s^2 + s g_m (C_1 + C_2) / C_1 C_2 + g_m/R_S C_1 C_2], \text{ when } g_m \cdot R_O \text{ is at least greater than } 10;$$

where s is a complex frequency= $j\omega$;

where j is an imaginary unit;

where $\omega = 2 \cdot \pi \cdot$ frequency;

where C_1 represents the capacitance value of C_1 ;

where C_2 represents the capacitance value of C_2 ; and,

where g_m is the transconductance of the first FET.

* * * * *

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 10,291,226 B1
APPLICATION NO. : 16/143654
DATED : May 14, 2019
INVENTOR(S) : Adam Vishinsky

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Specification

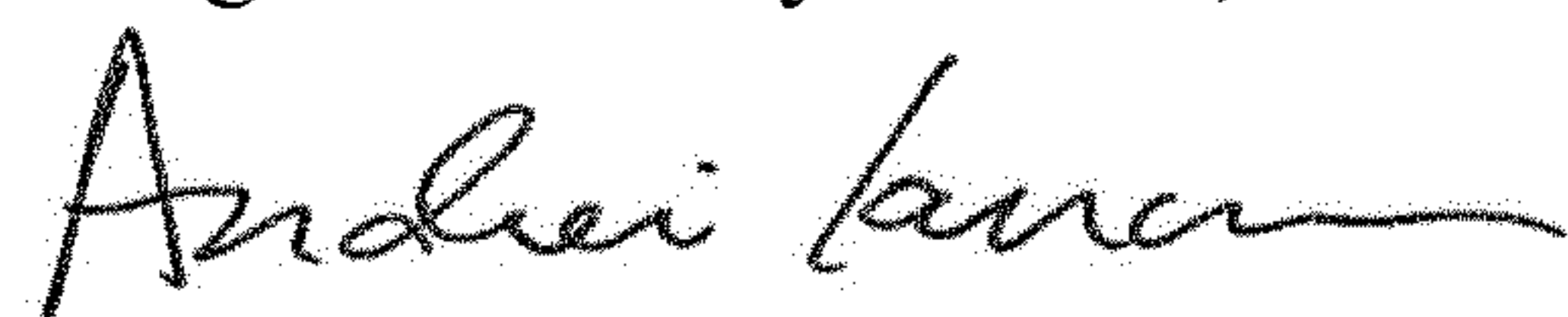
In Column 5, Line 57, two separate formulas have been so closely positioned so as to appear as if they are one formula, the formulas should be printed as follows:

$$V_o/V_s = g_m/(g_m + sC_1) \qquad V_o/V_{n,gm} = g_m/(g_m + sC_1)$$

In Column 6, Line 22, two separate formulas have been so closely positioned so as to appear as if they are one formula, the formulas should be printed as follows:

$$I_o/I_s = g_m/(g_m + sC_1) \qquad I_o/I_n = Sg_mC_1/(g_m + sC_1)$$

Signed and Sealed this
Eighteenth Day of June, 2019



Andrei Iancu
Director of the United States Patent and Trademark Office